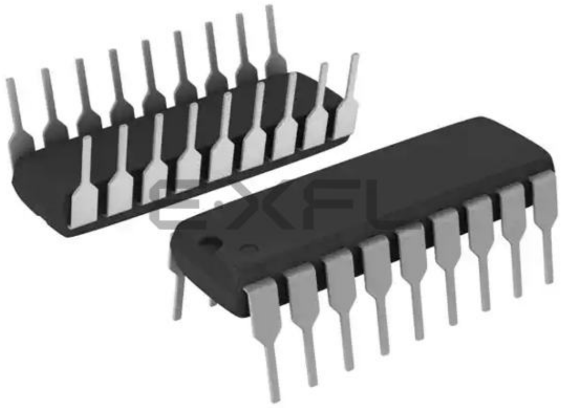

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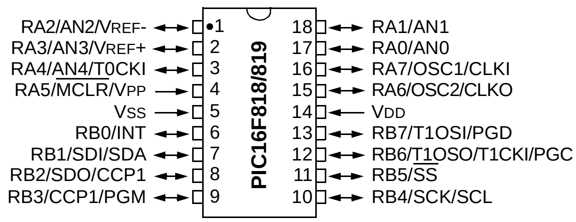
Applications of "Embedded - Microcontrollers"

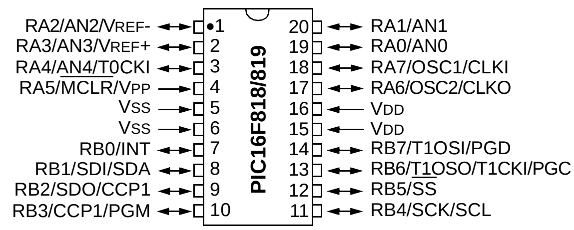
Details	
Product Status	Active
Core Processor	PIC
Core Size	8-Bit
Speed	20MHz
Connectivity	I²C, SPI
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	16
Program Memory Size	3.5KB (2K x 14)
Program Memory Type	FLASH
EEPROM Size	256 x 8
RAM Size	256 x 8
Voltage - Supply (Vcc/Vdd)	4V ~ 5.5V
Data Converters	A/D 5x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Through Hole
Package / Case	18-DIP (0.300", 7.62mm)
Supplier Device Package	18-PDIP
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic16f819-e-p

Pin Diagrams

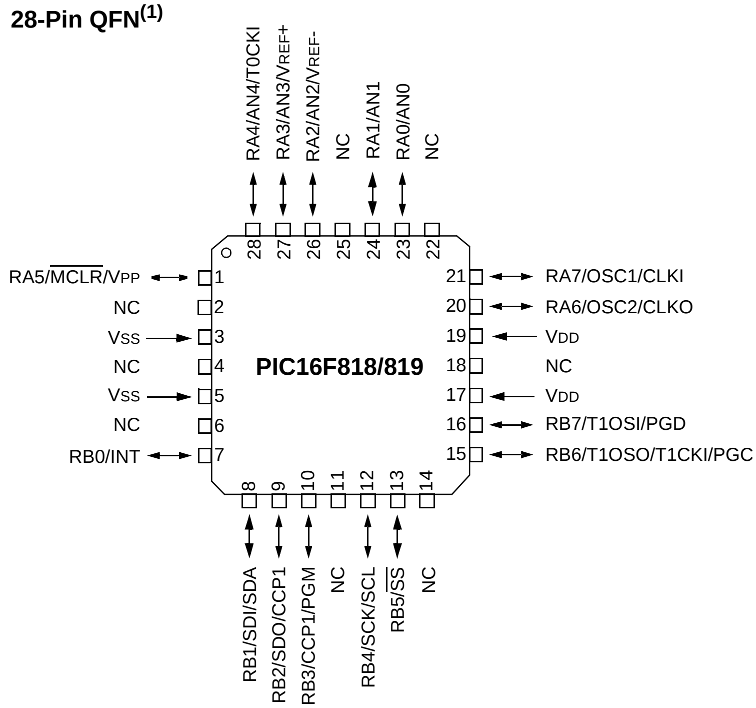
18-Pin PDIP, SOIC



20-Pin SSOP



28-Pin QFN(1)



Note 1: For the QFN package, it is recommended that the bottom pad be connected to VSS.

2.2.2.3 INTCON Register

The INTCON register is a readable and writable register that contains various enable and flag bits for the TMR0 register overflow, RB port change and external RB0/INT pin interrupts.

Note:	Interrupt flag bits get set when an interrupt condition occurs regardless of the state of its corresponding enable bit or the Global Interrupt Enable bit, GIE (INTCON<7>). User software should ensure the appropriate interrupt flag bits are clear prior to enabling an interrupt.

REGISTER 2-3: INTCON: INTERRUPT CONTROL REGISTER (ADDRESS 0Bh, 8Bh, 10Bh, 18Bh)

R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-x
GIE	PEIE	TMR0IE	INTE	RBIE	TMR0IF	INTF	RBIF
bit 7							bit 0

bit 7 **GIE:** Global Interrupt Enable bit
1 = Enables all unmasked interrupts
0 = Disables all interrupts

bit 6 **PEIE:** Peripheral Interrupt Enable bit
1 = Enables all unmasked peripheral interrupts
0 = Disables all peripheral interrupts

bit 5 **TMR0IE:** TMR0 Overflow Interrupt Enable bit
1 = Enables the TMR0 interrupt
0 = Disables the TMR0 interrupt

bit 4 **INTE:** RB0/INT External Interrupt Enable bit
1 = Enables the RB0/INT external interrupt
0 = Disables the RB0/INT external interrupt

bit 3 **RBIE:** RB Port Change Interrupt Enable bit
1 = Enables the RB port change interrupt
0 = Disables the RB port change interrupt

bit 2 **TMR0IF:** TMR0 Overflow Interrupt Flag bit
1 = TMR0 register has overflowed (must be cleared in software)
0 = TMR0 register did not overflow

bit 1 **INTF:** RB0/INT External Interrupt Flag bit
1 = The RB0/INT external interrupt occurred (must be cleared in software)
0 = The RB0/INT external interrupt did not occur

bit 0 **RBIF:** RB Port Change Interrupt Flag bit
A mismatch condition will continue to set flag bit RBIF. Reading PORTB will end the mismatch condition and allow flag bit RBIF to be cleared.
1 = At least one of the RB7:RB4 pins changed state (must be cleared in software)
0 = None of the RB7:RB4 pins have changed state

Legend:			
R = Readable bit	W = Writable bit	U = Unimplemented bit, read as ‘0’	
-n = Value at POR	‘1’ = Bit is set	‘0’ = Bit is cleared	x = Bit is unknown

3.7 Writing to Flash Program Memory

Flash program memory may only be written to if the destination address is in a segment of memory that is not write-protected, as defined in bits WRT1:WRT0 of the device Configuration Word (Register 12-1). Flash program memory must be written in four-word blocks. A block consists of four words with sequential addresses, with a lower boundary defined by an address, where EEADR<1:0> = `00`. At the same time, all block writes to program memory are done as write-only operations. The program memory must first be erased. The write operation is edge-aligned and cannot occur across boundaries.

To write to the program memory, the data must first be loaded into the buffer registers. There are four 14-bit buffer registers and they are addressed by the low 2 bits of EEADR.

The following sequence of events illustrate how to perform a write to program memory:

- Set the EEPGD and WREN bits in the EECON1 register
- Clear the FREE bit in EECON1
- Write address to EEADRH:EEADR
- Write data to EEDATH:EEDATA
- Write 55 to EECON2
- Write AA to EECON2
- Set WR bit in EECON 1

The user must follow the same specific sequence to initiate the write for each word in the program block by writing each program word in sequence (`00, 01, 10, 11`).

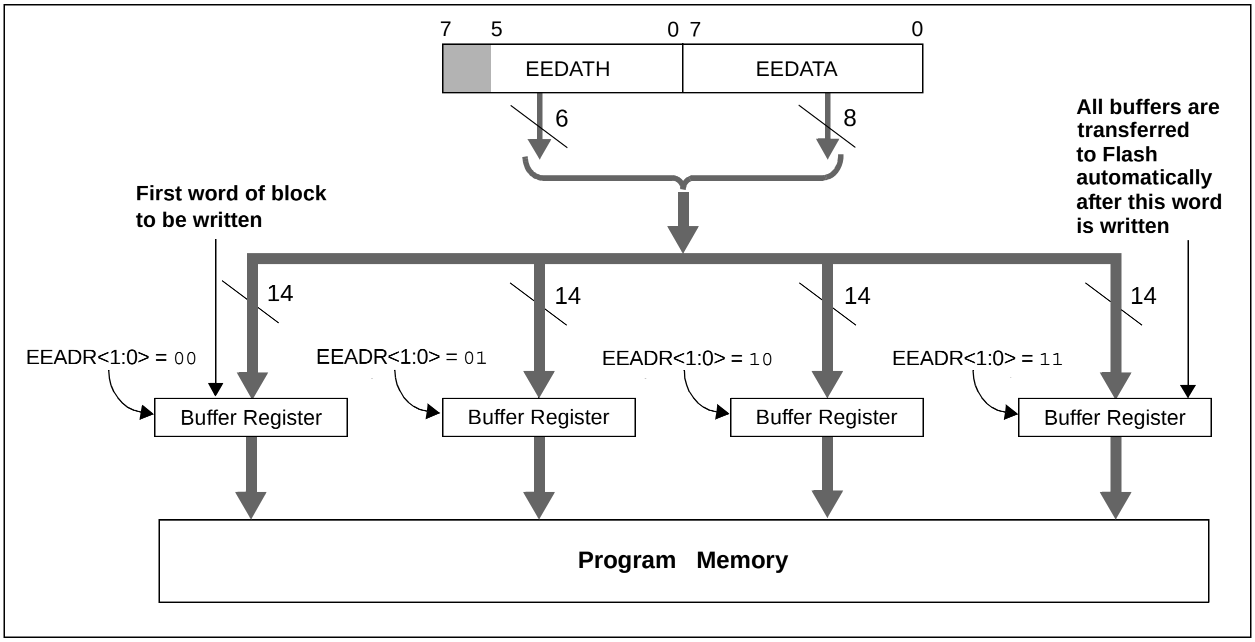
There are 4 buffer register words and all four locations **MUST** be written to with correct data.

After the "`BSF EECON1, WR`" instruction, if EEADR ≠ `xxxxxx11`, then a short write will occur. This short write-only transfers the data to the buffer register. The WR bit will be cleared in hardware after one cycle.

After the "`BSF EECON1, WR`" instruction, if EEADR = `xxxxxx11`, then a long write will occur. This will simultaneously transfer the data from EEDATH:EEDATA to the buffer registers and begin the write of all four words. The processor will execute the next instruction and then ignore the subsequent instruction. The user should place `NOP` instructions into the second words. The processor will then halt internal operations for typically 2 msec in which the write takes place. This is not a Sleep mode, as the clocks and peripherals will continue to run. After the write cycle, the processor will resume operation with the 3rd instruction after the EECON1 write instruction.

After each long write, the 4 buffer registers will be reset to 3FFF.

FIGURE 3-1: BLOCK WRITES TO FLASH PROGRAM MEMORY



An example of the complete four-word write sequence is shown in Example 3-5. The initial address is loaded into the EEADRH:EEADR register pair; the four words of data are loaded using indirect addressing, assuming that a row erase sequence has already been performed.

EXAMPLE 3-5: WRITING TO FLASH PROGRAM MEMORY

```
; This write routine assumes the following:

; 1. The 32 words in the erase block have already been erased.
; 2. A valid starting address (the least significant bits = '00') is loaded into EEADRH:EEADR
; 3. This example is starting at 0x100, this is an application dependent setting.
; 4. The 8 bytes (4 words) of data are loaded, starting at an address in RAM called ARRAY.
; 5. This is an example only, location of data to program is application dependent.
; 6. word_block is located in data memory.

        BANKSEL  EECON1              ;prepare for WRITE procedure
        BSF      EECON1, EEPGD       ;point to program memory
        BSF      EECON1, WREN        ;allow write cycles
        BCF      EECON1, FREE        ;perform write only

        BANKSEL  word_block
        MOVLW    .4
        MOVWF    word_block          ;prepare for 4 words to be written

        BANKSEL  EEADRH              ;Start writing at 0x100
        MOVLW    0x01
        MOVWF    EEADRH              ;load HIGH address
        MOVLW    0x00
        MOVWF    EEADR               ;load LOW address
        BANKSEL  ARRAY
        MOVLW    ARRAY               ;initialize FSR to start of data
        MOVWF    FSR
LOOP
        BANKSEL  EEDATA
        MOVF     INDF, W             ;indirectly load EEDATA
        MOVWF    EEDATA
        INCF     FSR, F              ;increment data pointer
        MOVF     INDF, W             ;indirectly load EEDATH
        MOVWF    EEDATH
        INCF     FSR, F              ;increment data pointer

        BANKSEL  EECON1
        MOVLW    0x55                ;required sequence
        MOVWF    EECON2
        MOVLW    0xAA
        MOVWF    EECON2
        BSF      EECON1, WR          ;set WR bit to begin write
        NOP                          ;instructions here are ignored as processor
        NOP

        BANKSEL  EEADR
        INCF     EEADR, f            ;load next word address
        BANKSEL  word_block
        DECFSZ   word_block, f       ;have 4 words been written?
        GOTO     loop                ;NO, continue with writing

        BANKSEL  EECON1
        BCF      EECON1, WREN        ;YES, 4 words complete, disable writes
        BSF      INTCON, GIE         ;enable interrupts
```

Required Sequence

3.8 Protection Against Spurious Write

There are conditions when the device should not write to the data EEPROM memory. To protect against spurious EEPROM writes, various mechanisms have been built-in. On power-up, WREN is cleared. Also, the Power-up Timer (72 ms duration) prevents an EEPROM write.

The write initiate sequence and the WREN bit together help prevent an accidental write during brown-out, power glitch or software malfunction.

3.9 Operation During Code-Protect

When the data EEPROM is code-protected, the microcontroller can read and write to the EEPROM normally. However, all external access to the EEPROM is disabled. External write access to the program memory is also disabled.

When program memory is code-protected, the microcontroller can read and write to program memory normally as well as execute instructions. Writes by the device may be selectively inhibited to regions of the memory depending on the setting of bits, WRT1:WRT0, of the Configuration Word (see **Section 12.1 "Configuration Bits"** for additional information). External access to the memory is also disabled.

TABLE 3-1: REGISTERS/BITS ASSOCIATED WITH DATA EEPROM AND FLASH PROGRAM MEMORIES

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Value on Power-on Reset	Value on all other Resets
10Ch	EEDATA	EEPROM/Flash Data Register Low Byte								xxxx xxxx	uuuu uuuu
10Dh	EEADR	EEPROM/Flash Address Register Low Byte								xxxx xxxx	uuuu uuuu
10Eh	EEDATH	—	—	EEPROM/Flash Data Register High Byte						--xx xxxx	--uu uuuu
10Fh	EEADRH	—	—	—	—	—	EEPROM/Flash Address Register High Byte			---- -xxx	---- -uuu
18Ch	EECON1	EEPGD	—	—	FREE	WRERR	WREN	WR	RD	x--x x000	x--x q000
18Dh	EECON2	EEPROM Control Register 2 (not a physical register)								---- ----	---- ----
0Dh	PIR2	—	—	—	EEIF	—	—	—	—	---0 ----	---0 ----
8Dh	PIE2	—	—	—	EEIE	—	—	—	—	---0 ----	---0 ----

Legend: x = unknown, u = unchanged, - = unimplemented, read as '0', q = value depends upon condition.
Shaded cells are not used by data EEPROM or Flash program memory.

4.0 OSCILLATOR CONFIGURATIONS

4.1 Oscillator Types

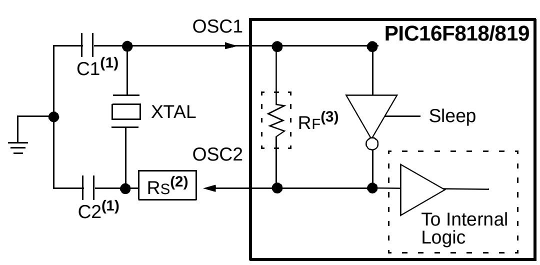
The PIC16F818/819 can be operated in eight different oscillator modes. The user can program three configuration bits (FOSC2:FOSC0) to select one of these eight modes (modes 5-8 are new PIC16 oscillator configurations):

1. LP — Low-Power Crystal
2. XT — Crystal/Resonator
3. HS — High-Speed Crystal/Resonator
4. RC — External Resistor/Capacitor with FOSC/4 output on RA6
5. RCIO — External Resistor/Capacitor with I/O on RA6
6. INTIO1 — Internal Oscillator with FOSC/4 output on RA6 and I/O on RA7
7. INTIO2 — Internal Oscillator with I/O on RA6 and RA7
8. ECIO — External Clock with I/O on RA6

4.2 Crystal Oscillator/Ceramic Resonators

In XT, LP or HS modes, a crystal or ceramic resonator is connected to the OSC1/CLKI and OSC2/CLKO pins to establish oscillation (see Figure 4-1 and Figure 4-2). The PIC16F818/819 oscillator design requires the use of a parallel cut crystal. Use of a series cut crystal may give a frequency out of the crystal manufacturer's specifications.

FIGURE 4-1: CRYSTAL OPERATION (HS, XT OR LP OSC CONFIGURATION)



Note 1: See Table 4-1 for typical values of C1 and C2.

2: A series resistor (RS) may be required for AT strip cut crystals.

3: RF varies with the crystal chosen (typically between 2 MΩ to 10 MΩ).

TABLE 4-1: CAPACITOR SELECTION FOR CRYSTAL OSCILLATOR (FOR DESIGN GUIDANCE ONLY)

Osc Type	Crystal Freq	Typical Capacitor Values Tested: C1	C2
LP	32 kHz	33 pF	33 pF
	200 kHz	15 pF	15 pF
XT	200 kHz	56 pF	56 pF
	1 MHz	15 pF	15 pF
	4 MHz	15 pF	15 pF
HS	4 MHz	15 pF	15 pF
	8 MHz	15 pF	15 pF
	20 MHz	15 pF	15 pF

Capacitor values are for design guidance only.

These capacitors were tested with the crystals listed below for basic start-up and operation. These values were not optimized.

Different capacitor values may be required to produce acceptable oscillator operation. The user should test the performance of the oscillator over the expected VDD and temperature range for the application.

See the notes following this table for additional information.

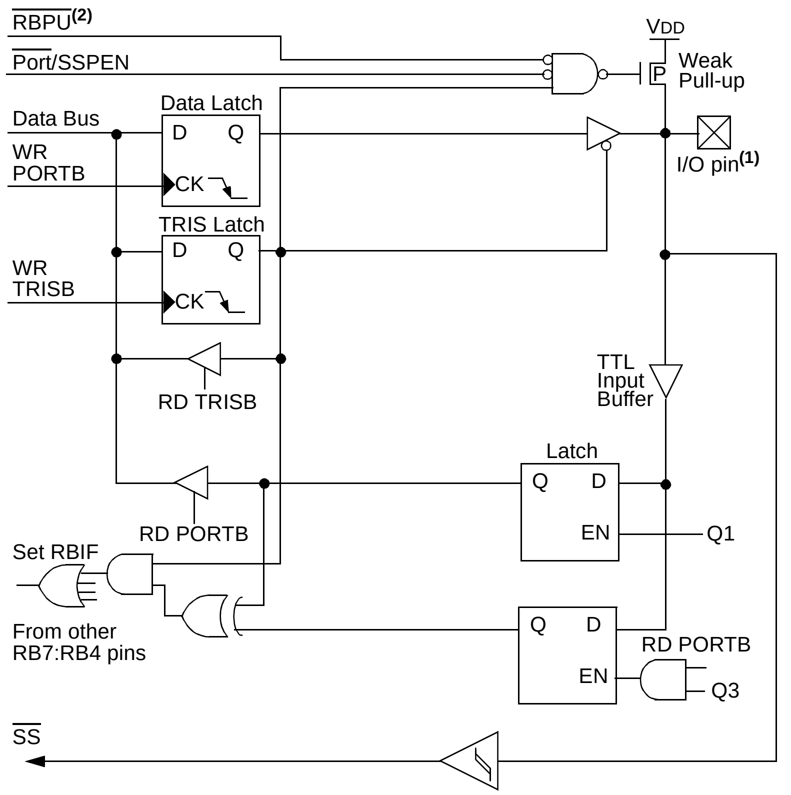
Note 1: Higher capacitance increases the stability of the oscillator but also increases the start-up time.

2: Since each crystal has its own characteristics, the user should consult the crystal manufacturer for appropriate values of external components.

3: RS may be required in HS mode, as well as XT mode, to avoid overdriving crystals with low drive level specification.

4: Always verify oscillator performance over the VDD and temperature range that is expected for the application.

FIGURE 5-13: BLOCK DIAGRAM OF RB5 PIN



Note 1: I/O pins have diode protection to VDD and VSS.

2: To enable weak pull-ups, set the appropriate TRIS bit(s) and clear the $\overline{\text{RBPU}}$ bit.

6.0 TIMER0 MODULE

The Timer0 module timer/counter has the following features:

- 8-bit timer/counter
- Readable and writable
- 8-bit software programmable prescaler
- Internal or external clock select
- Interrupt-on-overflow from FFh to 00h
- Edge select for external clock

Additional information on the Timer0 module is available in the *"PIC® Mid-Range MCU Family Reference Manual"* (DS33023).

Figure 6-1 is a block diagram of the Timer0 module and the prescaler shared with the WDT.

6.1 Timer0 Operation

Timer0 operation is controlled through the OPTION_REG register (see Register 2-2). Timer mode is selected by clearing bit T0CS (OPTION_REG<5>). In Timer mode, the Timer0 module will increment every instruction cycle (without prescaler). If the TMR0 register is written, the increment is inhibited for the following two instruction cycles. The user can work around this by writing an adjusted value to the TMR0 register.

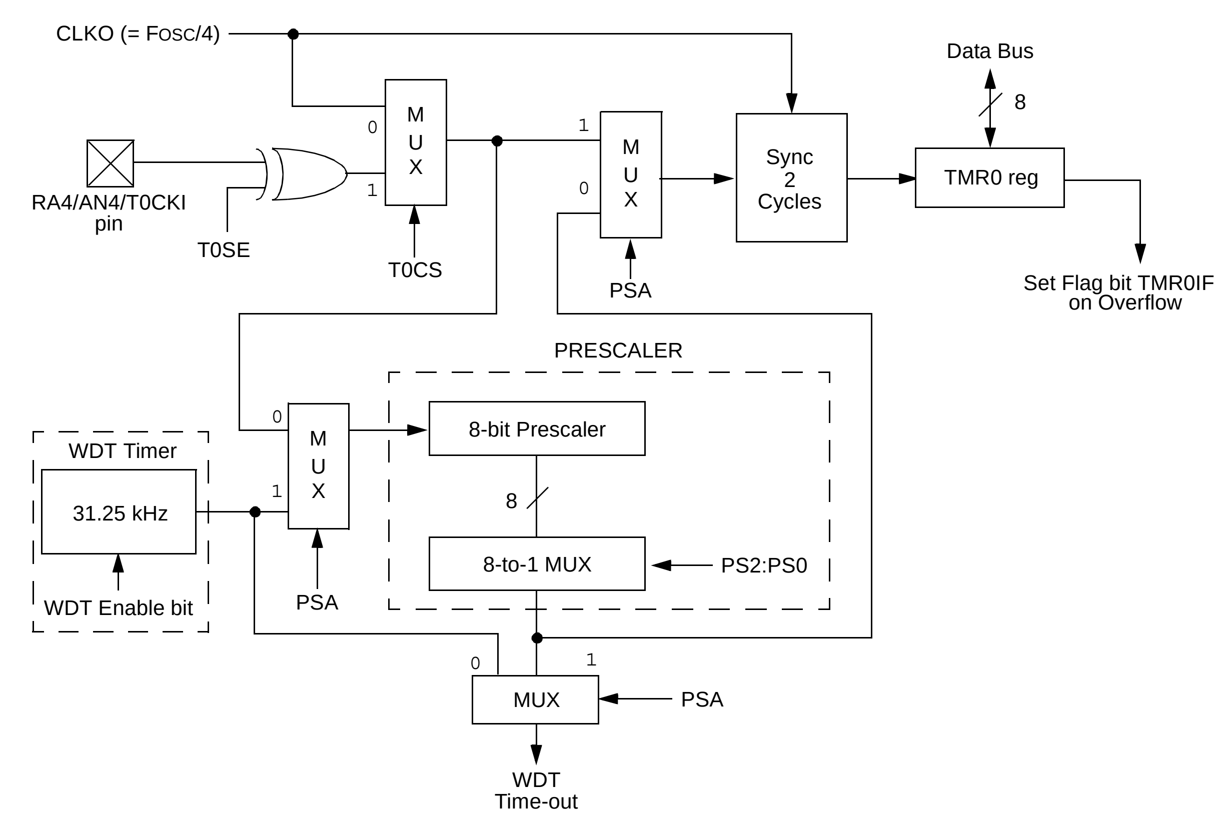
Counter mode is selected by setting bit T0CS (OPTION_REG<5>). In Counter mode, Timer0 will increment either on every rising or falling edge of pin RA4/AN4/T0CKI. The incrementing edge is determined by the Timer0 Source Edge Select bit, T0SE (OPTION_REG<4>). Clearing bit T0SE selects the rising edge. Restrictions on the external clock input are discussed in detail in **Section 6.3 "Using Timer0 with an External Clock"**.

The prescaler is mutually exclusively shared between the Timer0 module and the Watchdog Timer. The prescaler is not readable or writable. **Section 6.4 "Prescaler"** details the operation of the prescaler.

6.2 Timer0 Interrupt

The TMR0 interrupt is generated when the TMR0 register overflows from FFh to 00h. This overflow sets bit, TMR0IF (INTCON<2>). The interrupt can be masked by clearing bit, TMR0IE (INTCON<5>). Bit TMR0IF must be cleared in software by the Timer0 module Interrupt Service Routine before re-enabling this interrupt. The TMR0 interrupt cannot awaken the processor from Sleep since the timer is shut-off during Sleep.

FIGURE 6-1: BLOCK DIAGRAM OF THE TIMER0/WDT PRESCALER



Note: T0CS, T0SE, PSA, PS2:PS0 are (OPTION_REG<5:0>).

7.5 Timer1 Operation in Asynchronous Counter Mode

If control bit, $\overline{\text{T1SYNC}}$ (T1CON<2>), is set, the external clock input is not synchronized. The timer continues to increment asynchronous to the internal phase clocks. The timer will continue to run during Sleep and can generate an interrupt on overflow that will wake-up the processor. However, special precautions in software are needed to read/write the timer.

In Asynchronous Counter mode, Timer1 cannot be used as a time base for capture or compare operations.

7.5.1 READING AND WRITING TIMER1 IN ASYNCHRONOUS COUNTER MODE

Reading TMR1H or TMR1L while the timer is running from an external asynchronous clock will ensure a valid read (taken care of in hardware). However, the user should keep in mind that reading the 16-bit timer in two 8-bit values itself poses certain problems, since the timer may overflow between the reads.

For writes, it is recommended that the user simply stop the timer and write the desired values. A write contention may occur by writing to the timer registers while the register is incrementing. This may produce an unpredictable value in the timer register.

Reading the 16-bit value requires some care. The example codes provided in Example 7-1 and Example 7-2 demonstrate how to write to and read Timer1 while it is running in Asynchronous mode.

EXAMPLE 7-1: WRITING A 16-BIT FREE RUNNING TIMER

```
; All interrupts are disabled
CLRF     TMR1L        ; Clear Low byte, Ensures no rollover into TMR1H
MOVLW    HI_BYTE      ; Value to load into TMR1H
MOVWF    TMR1H, F     ; Write High byte
MOVLW    LO_BYTE      ; Value to load into TMR1L
MOVWF    TMR1H, F     ; Write Low byte
; Re-enable the Interrupt (if required)
CONTINUE              ; Continue with your code
```

EXAMPLE 7-2: READING A 16-BIT FREE RUNNING TIMER

```
; All interrupts are disabled
MOVF     TMR1H, W     ; Read high byte
MOVWF    TMPH
MOVF     TMR1L, W     ; Read low byte
MOVWF    TMPL
MOVF     TMR1H, W     ; Read high byte
SUBWF    TMPH, W      ; Sub 1st read with 2nd read
BTFSC    STATUS, Z    ; Is result = 0
GOTO     CONTINUE     ; Good 16-bit read
; TMR1L may have rolled over between the read of the high and low bytes.
; Reading the high and low bytes now will read a good value.
MOVF     TMR1H, W     ; Read high byte
MOVWF    TMPH
MOVF     TMR1L, W     ; Read low byte
MOVWF    TMPL         ; Re-enable the Interrupt (if required)
CONTINUE              ; Continue with your code
```

9.0 CAPTURE/COMPARE/PWM (CCP) MODULE

The Capture/Compare/PWM (CCP) module contains a 16-bit register that can operate as a:

- 16-bit Capture register
- 16-bit Compare register
- PWM Master/Slave Duty Cycle register

Table 9-1 shows the timer resources of the CCP module modes.

Capture/Compare/PWM Register 1 (CCPR1) is comprised of two 8-bit registers: CCPR1L (low byte) and CCPR1H (high byte). The CCP1CON register controls the operation of CCP1. The special event trigger is generated by a compare match which will reset Timer1 and start an A/D conversion (if the A/D module is enabled).

The CCP module's input/output pin (CCP1) can be configured as RB2 or RB3. This selection is set in bit 12 (CCPMX) of the Configuration Word register.

Additional information on the CCP module is available in the *"PIC® Mid-Range MCU Family Reference Manual"* (DS33023) and in Application Note *AN594, "Using the CCP Module(s)"* (DS00594).

TABLE 9-1: CCP MODE – TIMER RESOURCE

CCP Mode	Timer Resource
Capture	Timer1
Compare	Timer1
PWM	Timer2

REGISTER 9-1: CCP1CON: CAPTURE/COMPARE/PWM CONTROL REGISTER 1 (ADDRESS 17h)

U-0	U-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0
—	—	CCP1X	CCP1Y	CCP1M3	CCP1M2	CCP1M1	CCP1M0
bit 7							bit 0

bit 7-6 **Unimplemented:** Read as '0'

bit 5-4 **CCP1X:CCP1Y:** PWM Least Significant bits

Capture mode:
Unused.

Compare mode:
Unused.

PWM mode:
These bits are the two LSbs of the PWM duty cycle. The eight MSbs are found in CCPRxL.

bit 3-0 **CCP1M3:CCP1M0:** CCP1 Mode Select bits

0000 = Capture/Compare/PWM disabled (resets CCP1 module)
0100 = Capture mode, every falling edge
0101 = Capture mode, every rising edge
0110 = Capture mode, every 4th rising edge
0111 = Capture mode, every 16th rising edge
1000 = Compare mode, set output on match (CCP1IF bit is set)
1001 = Compare mode, clear output on match (CCP1IF bit is set)
1010 = Compare mode, generate software interrupt on match (CCP1IF bit is set, CCP1 pin is unaffected)
1011 = Compare mode, trigger special event (CCP1IF bit is set, CCP1 pin is unaffected); CCP1 resets TMR1 and starts an A/D conversion (if A/D module is enabled)
11xx = PWM mode

Legend:			
R = Readable bit	W = Writable bit	U = Unimplemented bit, read as '0'	
-n = Value at POR	'1' = Bit is set	'0' = Bit is cleared	x = Bit is unknown

The maximum PWM resolution (bits) for a given PWM frequency is given by the following formula.

EQUATION 9-3:

$$\text{Resolution} = \frac{\log\left(\frac{F_{OSC}}{F_{PWM}}\right)}{\log(2)} \text{ bits}$$

Note:	If the PWM duty cycle value is longer than the PWM period, the CCP1 pin will not be cleared.

9.3.3 SETUP FOR PWM OPERATION

The following steps should be taken when configuring the CCP module for PWM operation:

1. Set the PWM period by writing to the PR2 register.
2. Set the PWM duty cycle by writing to the CCPR1L register and CCP1CON<5:4> bits.
3. Make the CCP1 pin an output by clearing the TRISB<x> bit.
4. Set the TMR2 prescale value and enable Timer2 by writing to T2CON.
5. Configure the CCP1 module for PWM operation.

Note:	The TRISB bit (2 or 3) is dependant upon the setting of configuration bit 12 (CCPMX).

TABLE 9-3: EXAMPLE PWM FREQUENCIES AND RESOLUTIONS AT 20 MHz

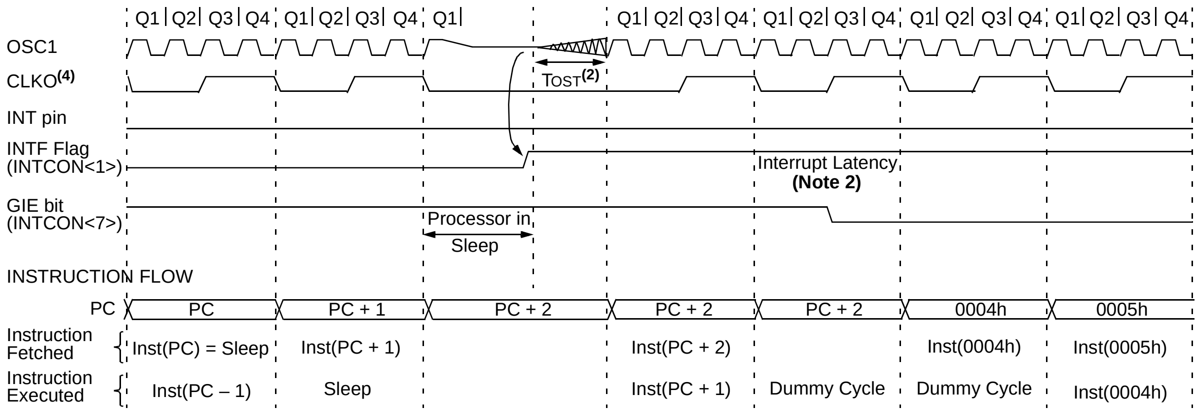
PWM Frequency	1.22 kHz	4.88 kHz	19.53 kHz	78.12 kHz	156.3 kHz	208.3 kHz
Timer Prescaler (1, 4, 16)	16	4	1	1	1	1
PR2 Value	0xFF	0xFF	0xFF	0x3F	0x1F	0x17
Maximum Resolution (bits)	10	10	10	8	7	5.5

TABLE 9-4: REGISTERS ASSOCIATED WITH PWM AND TIMER2

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Value on POR, BOR	Value on all other Resets
0Bh,8Bh 10Bh,18Bh	INTCON	GIE	PEIE	TMR0IE	INTE	RBIE	TMR0IF	INTF	RBIF	0000 000x	0000 000u
0Ch	PIR1	—	ADIF	—	—	SSPIF	CCP1IF	TMR2IF	TMR1IF	-0-- 0000	-0-- 0000
8Ch	PIE1	—	ADIE	—	—	SSPIE	CCP1IE	TMR2IE	TMR1IE	-0-- 0000	-0-- 0000
86h	TRISB	PORTB Data Direction Register								1111 1111	1111 1111
11h	TMR2	Timer2 Module Register								0000 0000	0000 0000
92h	PR2	Timer2 Module Period Register								1111 1111	1111 1111
12h	T2CON	—	TOUTPS3	TOUTPS2	TOUTPS1	TOUTPS0	TMR2ON	T2CKPS1	T2CKPS0	-000 0000	-000 0000
15h	CCPR1L	Capture/Compare/PWM Register 1 (LSB)								xxxx xxxx	uuuu uuuu
16h	CCPR1H	Capture/Compare/PWM Register 1 (MSB)								xxxx xxxx	uuuu uuuu
17h	CCP1CON	—	—	CCP1X	CCP1Y	CCP1M3	CCP1M2	CCP1M1	CCP1M0	--00 0000	--00 0000

Legend: x = unknown, u = unchanged, - = unimplemented, read as '0'. Shaded cells are not used by PWM and Timer2.

FIGURE 12-9: WAKE-UP FROM SLEEP THROUGH INTERRUPT



Note 1: XT, HS or LP Oscillator mode assumed.
2: TOST = 1024 TOSC (drawing not to scale). This delay will not be there for RC Oscillator mode.
3: GIE = `1` assumed. In this case, after wake-up, the processor jumps to the interrupt routine. If GIE = `0`, execution will continue in-line.
4: CLKO is not available in these oscillator modes but shown here for timing reference.

12.14 In-Circuit Debugger

When the DEBUG bit in the Configuration Word is programmed to a '`0`', the In-Circuit Debugger functionality is enabled. This function allows simple debugging functions when used with MPLAB® ICD. When the microcontroller has this feature enabled, some of the resources are not available for general use. Table 12-6 shows which features are consumed by the background debugger.

TABLE 12-6: DEBUGGER RESOURCES

I/O pins	RB6, RB7
Stack	1 level
Program Memory	Address 0000h must be `NOP`
	Last 100h words
Data Memory	0x070 (0x0F0, 0x170, 0x1F0) 0x1EB-0x1EF

To use the In-Circuit Debugger function of the microcontroller, the design must implement In-Circuit Serial Programming connections to $\overline{MCLR}$/VPP, VDD, GND, RB7 and RB6. This will interface to the in-circuit debugger module available from Microchip or one of the third party development tool companies.

12.15 Program Verification/Code Protection

If the code protection bit(s) have not been programmed, the on-chip program memory can be read out for verification purposes.

12.16 ID Locations

Four memory locations (2000h-2003h) are designated as ID locations, where the user can store checksum or other code identification numbers. These locations are not accessible during normal execution but are readable and writable during program/verify. It is recommended that only the four Least Significant bits of the ID location are used.

COMF	Complement f
Syntax:	[*label*] COMF f,d
Operands:	0 ≤ f ≤ 127 d ∈ [0,1]
Operation:	(f) → (destination)
Status Affected:	Z
Description:	The contents of register ‘f’ are complemented. If ‘d’ = `0`, the result is stored in W. If ‘d’ = `1`, the result is stored back in register ‘f’.

DECF	Decrement f
Syntax:	[*label*] DECF f,d
Operands:	0 ≤ f ≤ 127 d ∈ [0,1]
Operation:	(f) – 1 → (destination)
Status Affected:	Z
Description:	Decrement register ‘f’. If ‘d’ = `0`, the result is stored in the W register. If ‘d’ = `1`, the result is stored back in register ‘f’.

DECFSZ	Decrement f, Skip if 0
Syntax:	[*label*] DECFSZ f,d
Operands:	0 ≤ f ≤ 127 d ∈ [0,1]
Operation:	(f) – 1 → (destination); skip if result = `0`
Status Affected:	None
Description:	The contents of register ‘f’ are decremented. If ‘d’ = `0`, the result is placed in the W register. If ‘d’ = `1`, the result is placed back in register ‘f’. If the result is ‘`1`’, the next instruction is executed. If the result is ‘`0`’, then a `NOP` is executed instead, making it a 2 TCY instruction.

GOTO	Unconditional Branch
Syntax:	[*label*] GOTO k
Operands:	0 ≤ k ≤ 2047
Operation:	k → PC<10:0> PCLATH<4:3> → PC<12:11>
Status Affected:	None
Description:	`GOTO` is an unconditional branch. The eleven-bit immediate value is loaded into PC bits<10:0>. The upper bits of PC are loaded from PCLATH<4:3>. `GOTO` is a two-cycle instruction.

INCF	Increment f
Syntax:	[*label*] INCF f,d
Operands:	0 ≤ f ≤ 127 d ∈ [0,1]
Operation:	(f) + 1 → (destination)
Status Affected:	Z
Description:	The contents of register ‘f’ are incremented. If ‘d’ = `0`, the result is placed in the W register. If ‘d’ = `1`, the result is placed back in register ‘f’.

INCFSZ	Increment f, Skip if 0
Syntax:	[*label*] INCFSZ f,d
Operands:	0 ≤ f ≤ 127 d ∈ [0,1]
Operation:	(f) + 1 → (destination), skip if result = `0`
Status Affected:	None
Description:	The contents of register ‘f’ are incremented. If ‘d’ = `0`, the result is placed in the W register. If ‘d’ = `1`, the result is placed back in register ‘f’. If the result is ‘`1`’, the next instruction is executed. If the result is ‘`0`’, a `NOP` is executed instead, making it a 2 TCY instruction.

15.2 DC Characteristics: Power-Down and Supply Current PIC16F818/819 (Industrial, Extended) PIC16LF818/819 (Industrial) (Continued)

PIC16LF818/819 (Industrial)	Standard Operating Conditions (unless otherwise stated) Operating temperature -40°C ≤ TA ≤ +85°C for industrial					
PIC16F818/819 (Industrial, Extended)	**Standard Operating Conditions (unless otherwise stated)** Operating temperature -40°C ≤ TA ≤ +85°C for industrial -40°C ≤ TA ≤ +125°C for extended					
Param No.	**Device**	**Typ**	**Max**	**Units**	**Conditions**	
	Supply Current (IDD)(2,3)					
	PIC16LF818/819	72	95	μA	-40°C	VDD = 2.0V	FOSC = 1 MHz (RC Oscillator)(3)
		76	90	μA	+25°C		
		76	90	μA	+85°C		
	PIC16LF818/819	138	175	μA	-40°C	VDD = 3.0V	
		136	170	μA	+25°C		
		136	170	μA	+85°C		
	All devices	310	380	μA	-40°C	VDD = 5.0V	
		290	360	μA	+25°C		
		280	360	μA	+85°C		
	Extended devices	350	500	μA	+125°C		
	PIC16LF818/819	270	315	μA	-40°C	VDD = 2.0V	FOSC = 4 MHz (RC Oscillator)(3)
		280	310	μA	+25°C		
		285	310	μA	+85°C		
	PIC16LF818/819	460	610	μA	-40°C	VDD = 3.0V	
		450	600	μA	+25°C		
		450	600	μA	+85°C		
	All devices	900	1060	μA	-40°C	VDD = 5.0V	
		890	1050	μA	+25°C		
		890	1050	μA	+85°C		
	Extended devices	.920	1.5	mA	+125°C		

Legend: Shading of rows is to assist in readability of the table.

Note 1: The power-down current in Sleep mode does not depend on the oscillator type. Power-down current is measured with the part in Sleep mode, with all I/O pins in high-impedance state and tied to VDD or VSS and all features that add delta current disabled (such as WDT, Timer1 Oscillator, BOR, etc.).

2: The supply current is mainly a function of operating voltage, frequency and mode. Other factors, such as I/O pin loading and switching rate, oscillator type and circuit, internal code execution pattern and temperature, also have an impact on the current consumption.
The test conditions for all IDD measurements in active operation mode are:
OSC1 = external square wave, from rail-to-rail; all I/O pins tri-stated, pulled to VDD;
MCLR = VDD; WDT enabled/disabled as specified.

3: For RC oscillator configurations, current through REXT is not included. The current through the resistor can be estimated by the formula Ir = VDD/2REXT (mA) with REXT in kΩ.

15.4 DC Characteristics: PIC16F818/819 (Industrial, Extended) PIC16LF818/819 (Industrial) (Continued)

DC CHARACTERISTICS			**Standard Operating Conditions (unless otherwise stated)** Operating temperature -40°C ≤ TA ≤ +85°C for industrial -40°C ≤ TA ≤ +125°C for extended Operating voltage VDD range as described in **Section 15.1 "DC Characteristics: Supply Voltage"**.				
Param No.	**Sym**	**Characteristic**	**Min**	**Typ†**	**Max**	**Units**	**Conditions**
	VOL	**Output Low Voltage**					
D080		I/O ports	—	—	0.6	V	IOL = 8.5 mA, VDD = 4.5V, -40°C to +125°C
D083		OSC2/CLKO (RC oscillator config)	—	—	0.6	V	IOL = 1.6 mA, VDD = 4.5V, -40°C to +125°C
	VOH	**Output High Voltage**					
D090		I/O ports **(Note 3)**	VDD – 0.7	—	—	V	IOH = -3.0 mA, VDD = 4.5V, -40°C to +125°C
D092		OSC2/CLKO (RC oscillator config)	VDD – 0.7	—	—	V	IOH = -1.3 mA, VDD = 4.5V, -40°C to +125°C
		Capacitive Loading Specs on Output Pins					
D100	COSC2	OSC2 pin	—	—	15	pF	In XT, HS and LP modes when external clock is used to drive OSC1
D101	CIO	All I/O pins and OSC2 (in RC mode)	—	—	50	pF	
D102	CB	SCL, SDA in I²C™ mode	—	—	400	pF	
		Data EEPROM Memory					
D120	ED	Endurance	100K	1M	—	E/W	-40°C to +85°C
			10K	100K	—	E/W	+85°C to +125°C
D121	VDRW	VDD for read/write	VMIN	—	5.5	V	Using EECON to read/write, VMIN = min. operating voltage
D122	TDEW	Erase/write cycle time	—	4	8	ms	
		Program Flash Memory					
D130	EP	Endurance	10K	100K	—	E/W	-40°C to +85°C
			1K	10K	—	E/W	+85°C to +125°C
D131	VPR	VDD for read	VMIN	—	5.5	V	
D132A		VDD for erase/write	VMIN	—	5.5	V	Using EECON to read/write, VMIN = min. operating voltage
D133	TPE	Erase cycle time	—	2	4	ms	
D134	TPW	Write cycle time	—	2	4	ms	

† Data in "Typ" column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

Note 1: In RC oscillator configuration, the OSC1/CLKI pin is a Schmitt Trigger input. It is not recommended that the PIC16F818/819 be driven with external clock in RC mode.

2: The leakage current on the $\overline{\text{MCLR}}$ pin is strongly dependent on the applied voltage level. The specified levels represent normal operating conditions. Higher leakage current may be measured at different input voltages.

3: Negative current is defined as current sourced by the pin.

TABLE 15-9: A/D CONVERTER CHARACTERISTICS: PIC16F818/819 (INDUSTRIAL, EXTENDED) PIC16LF818/819 (INDUSTRIAL)

Param No.	Sym	Characteristic		Min	Typ†	Max	Units	Conditions
A01	NR	Resolution		—	—	10-bits	bit	VREF = VDD = 5.12V, VSS ≤ VAIN ≤ VREF
A03	EIL	Integral Linearity Error		—	—	<±1	LSb	VREF = VDD = 5.12V, VSS ≤ VAIN ≤ VREF
A04	EDL	Differential Linearity Error		—	—	<±1	LSb	VREF = VDD = 5.12V, VSS ≤ VAIN ≤ VREF
A06	EOFF	Offset Error		—	—	<±2	LSb	VREF = VDD = 5.12V, VSS ≤ VAIN ≤ VREF
A07	EGN	Gain Error		—	—	<±1	LSb	VREF = VDD = 5.12V, VSS ≤ VAIN ≤ VREF
A10	—	Monotonicity		—	guaranteed(3)	—	—	VSS ≤ VAIN ≤ VREF
A20	VREF	Reference Voltage (VREF+ – VREF-)		2.0	—	VDD + 0.3	V	
A21	VREF+	Reference Voltage High		AVDD – 2.5V		AVDD + 0.3V	V	
A22	VREF-	Reference Voltage Low		AVSS – 0.3V		VREF+ – 2.0V	V	
A25	VAIN	Analog Input Voltage		VSS – 0.3V	—	VREF + 0.3V	V	
A30	ZAIN	Recommended Impedance of Analog Voltage Source		—	—	2.5	kΩ	**(Note 4)**
A40	IAD	A/D Conversion Current (VDD)	PIC16**F**818/819	—	220	—	μA	Average current consumption when A/D is on **(Note 1)**
			PIC16**LF**818/819	—	90	—	μA	
A50	IREF	VREF Input Current **(Note 2)**		—	—	5	μA	During VAIN acquisition. Based on differential of VHOLD to VAIN to charge CHOLD, see **Section 11.1 "A/D Acquisition Requirements"**.
				—	—	150	μA	During A/D conversion cycle

† Data in "Typ" column is at 5V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

Note 1: When A/D is off, it will not consume any current other than minor leakage current. The power-down current spec includes any such leakage from the A/D module.

2: VREF current is from RA3 pin or VDD pin, whichever is selected as reference input.

3: The A/D conversion result never decreases with an increase in the input voltage and has no missing codes.

4: Maximum allowed impedance for analog voltage source is 10 kΩ. This requires higher acquisition time.

FIGURE 16-19: TYPICAL, MINIMUM AND MAXIMUM VOL vs. IOL (VDD = 5V, -40°C TO +125°C)

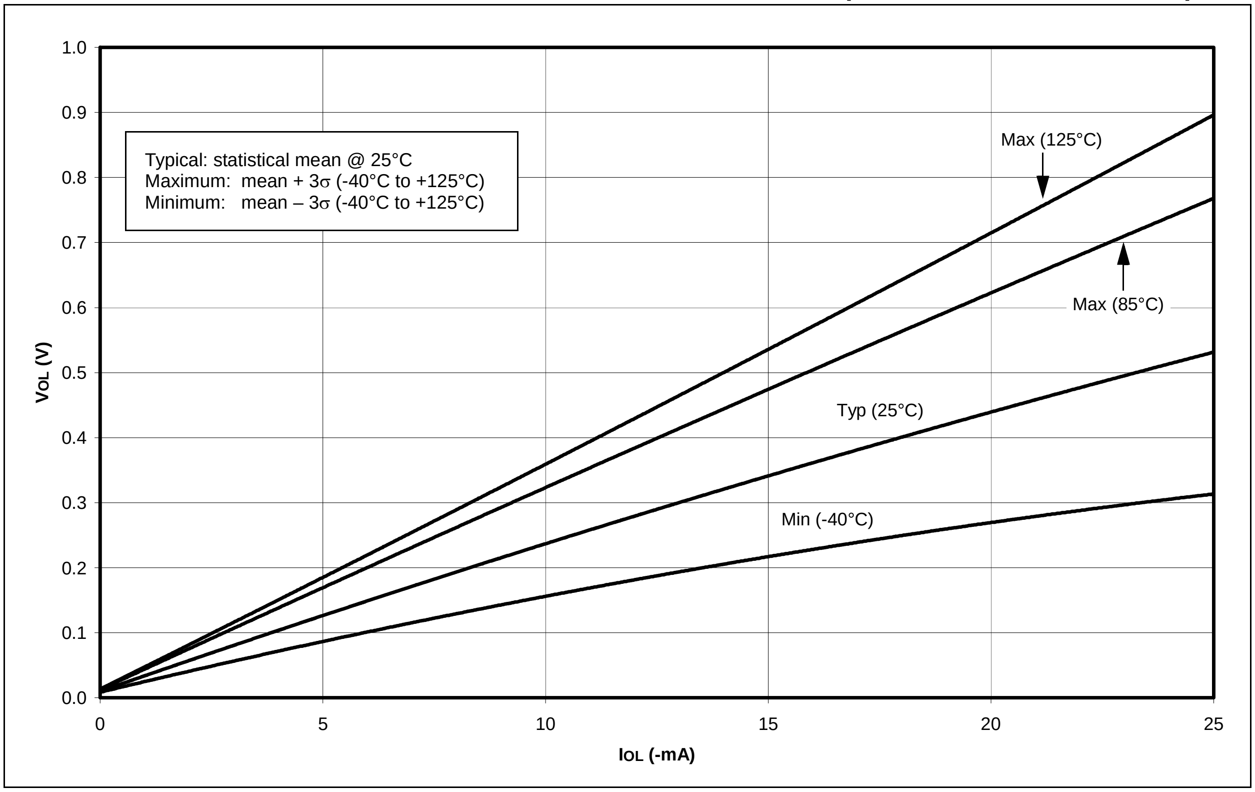
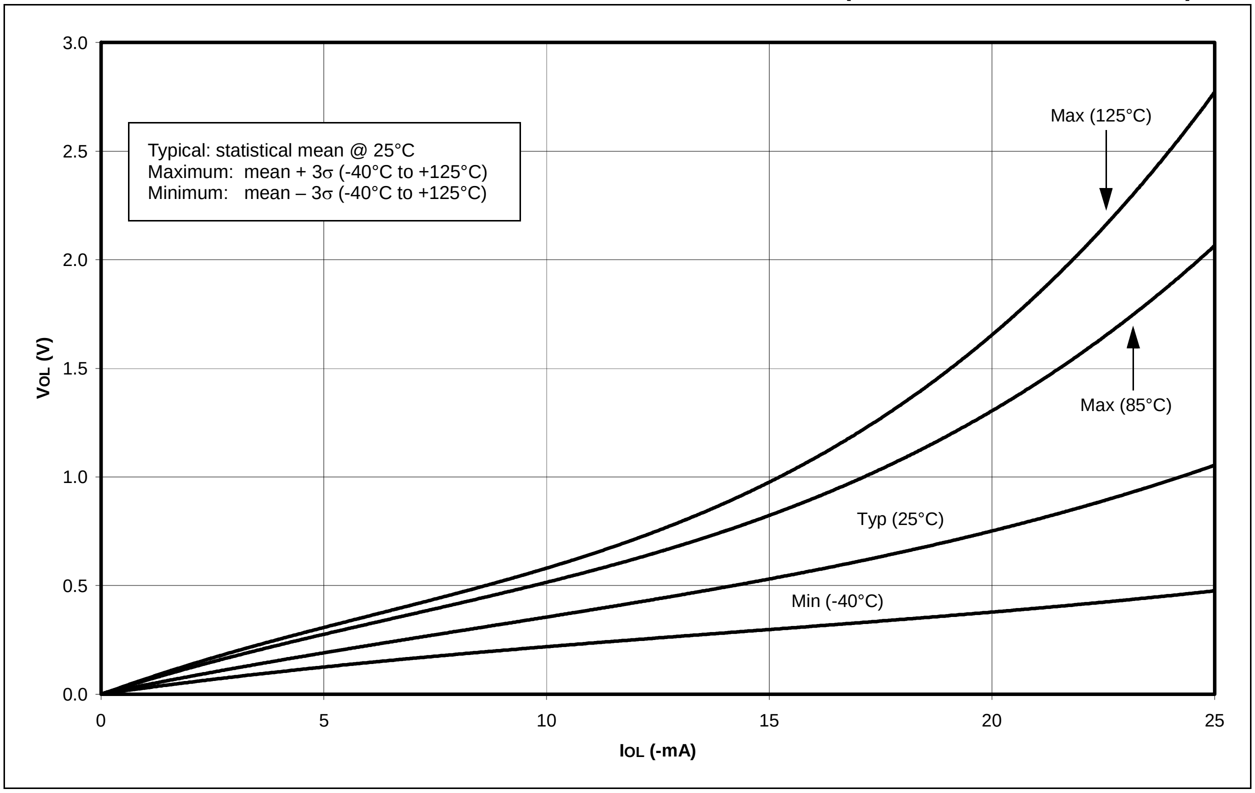


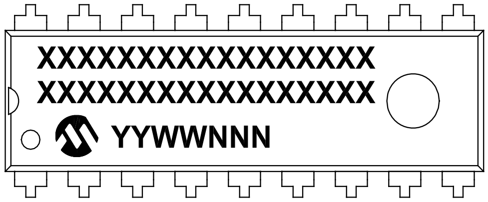
FIGURE 16-20: TYPICAL, MINIMUM AND MAXIMUM VOL vs. IOL (VDD = 3V, -40°C TO +125°C)



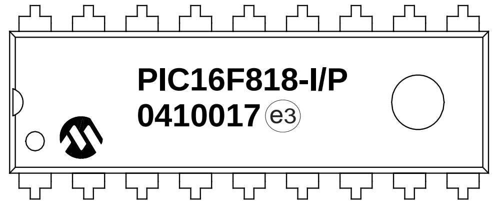
17.0 PACKAGING INFORMATION

17.1 Package Marking Information

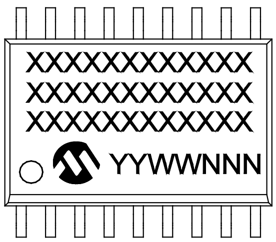
18-Lead PDIP (300 mil)



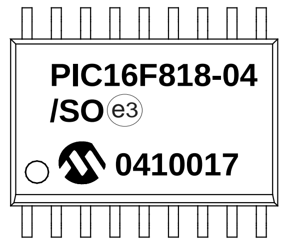
Example



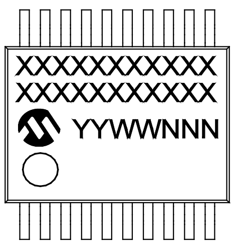
18-Lead SOIC (7.50 mm)



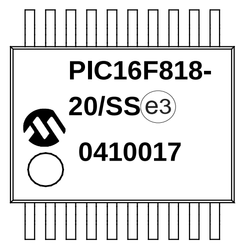
Example



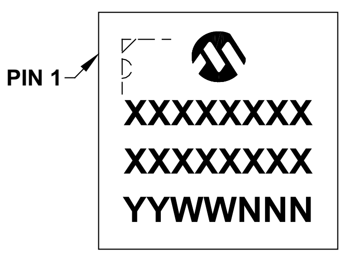
20-Lead SSOP (5.30 mm)



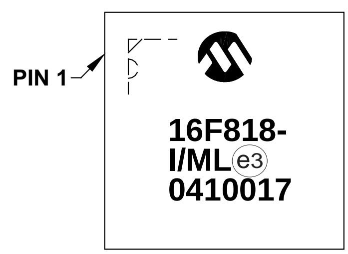
Example



28-Lead QFN (6x6 mm)



Example

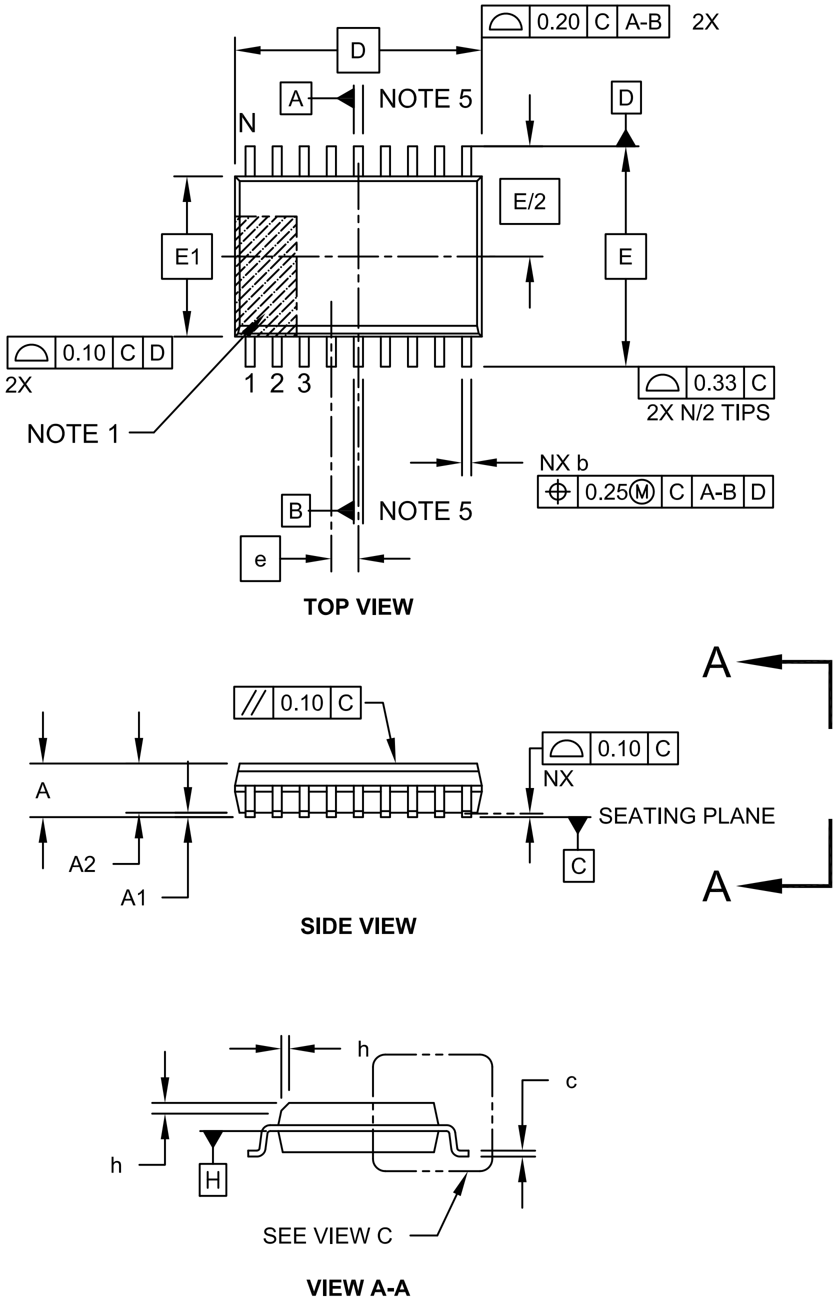


Legend:	XX...X	Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week ‘01’)
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

18-Lead Plastic Small Outline (SO) - Wide, 7.50 mm Body [SOIC]

Note:	For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-051C Sheet 1 of 2